

**1. Material** Substrate GaAlAs (N Type) Removed  
 Epitaxial Layer GaAlAs (P/N Type)

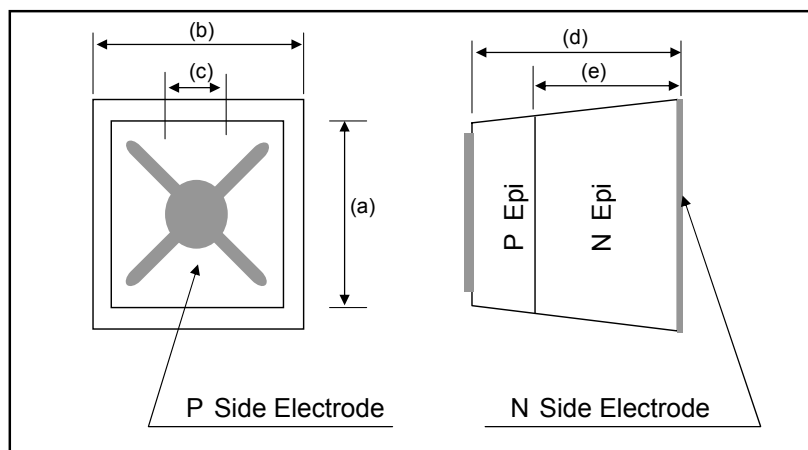
**2. Electrode** N(Cathode) Side Gold Alloy  
 P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$			1.58	V	IF=50mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Power	$P_O$	17	20		mW	IF=50mA
Wavelength	$\lambda_P$		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	$T_r$		22		ns	
Fall Time	$T_f$		13		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data** (a) Emission Area ----- 14.7mil x 14.7mil  
 (b) Bottom Area ----- 15.7mil x 15.7mil  
 (c) Bonding Pad ----- 128um  
 (d) Chip Thickness ----- 7mil  
 (e) Junction Height ----- 6.5mil



**AUK Corp.**

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea

Tel. +82 63 839 1111 Fax. +82 63 835 8259

[www.auk.co.kr](http://www.auk.co.kr)

